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## PMP40988\_GaN Card REV E2 Bill of Materials

Item #	Designator	Quantity	Value	PartNumber	Manufacturer	Description	PackageReference
1	IPCB1	1		PMP40988_GaN Card	Any	Printed Circuit Board	
2	C1, C36, C37	3	0.1uF	C1005X7R1H104K050BB	TDK	CAP, CERM, 0.1 uF, 50 V, +/- 10%, X7R, 0402	402
3	C2	1	4.7uF	GCM21BR71C475KA73L	MuRata	CAP, CERM, 4.7 uF, 16 V, +/- 10%, X7R, AEC-Q200 Grade 1, 0805	805
4	C3, C4, C13, C14, C16, C17	6	100pF	04025A101FAT2A	AVX	CAP, CERM, 100 pF, 50 V, +/- 1%, C0G/NP0, 0402	402
5	C5, C6, C7, C8, C39	5	1uF	C1005X5R1E105K050BC	TDK	CAP, CERM, 1 uF, 25 V, +/- 10%, X5R, 0402	402
6	C9, C10, C21	3	4.7uF	C1608X5R1V475K080AC	TDK	CAP, CERM, 4.7 uF, 35 V, +/- 10%, X5R, 0603	603
7	C11, C12	2	10uF	C3216X7R1E106M160AE	TDK	CAP, CERM, 10 uF, 25 V, +/- 20%, X7R, 1206_190	1206_190
8	C15, C19	2	0.22uF	CL05B224K05NNNC	Samsung Electro-Mechanics	CAP, CERM, 0.22 uF, 16 V, +/- 10%, X7R, 0402	402
9	C18, C20	2	2.2uF	GRT155R61E225KE13D	MuRata	CAP, CERM, 2.2 uF, 25 V, +/- 10%, X5R, AEC-Q200 Grade 3, 0402	402
10	C22, C23	2	0.022uF	C1206C223KDRACU	Kemet	CAP, CERM, 0.022 uF, 1000 V, +/- 10%, X7R, AEC-Q200 Grade 1, 1206	1206
11	C24, C25	2	0.1uF	C1812W104KDRACU	Kemet	CAP, CERM, 0.1 uF, 1000 V, +/- 10%, X7R, 1812	1812
12	C33, C34	2	43pF	GCQ1555C1H430JB01D	MuRata	CAP, CERM, 43 pF, 50 V, +/- 5%, C0G/NP0, AEC-Q200 Grade 1, 0402	402
13	C38	1	0.01uF	C0402C103K4RACTU	Kemet	CAP, CERM, 0.01 uF, 16 V, +/- 10%, X7R, 0402	402
14	D2, D3	2	20V	MBR0520LT1G	ON Semiconductor	Diode, Schottky, 20 V, 0.5 A, SOD-123	SOD-123
15	J1	1		M50-3900642	Harwin	Connector Header Through Hole, Right Angle 12 position 0.050" (1.27mm)	HDR12
16	L1, L2	2		SDEM20161T-4R7MS	Cyntec	4.7uH Unshielded Inductor 1.1A 426mOhm Max 0806 (2016 Metric)	SMD2
17	L3	1		ACM2520-601-2P-T002	TDK	Coupled inductor, 0.2 A, 0.45 ohm, SMD	2.5x2mm
18	Paux_RTN, SW, Vbulk1	6		3621-0-32-15-00-00-08-0	Mill-Max	PCB Pin, 0.04" DIA, Edge-Mount	PCB Pin, 0.04" DIA, R/A, Edge-Mount
19	R1, R2, R5, R6	4	49.9	RC0402FR-0749R9L	Yageo America	RES, 49.9, 1%, 0.063 W, 0402	402
20	R4, R10, R15	3	0	ERJ-2GE0R00X	Panasonic	RES, 0, 5%, 0.1 W, AEC-Q200 Grade 0, 0402	402
21	R8	1	0	ERJ-8GEY0R00V	Panasonic	RES, 0, 5%, 0.25 W, AEC-Q200 Grade 0, 1206	1206
22	R11, R12, R21, R22	4	300	CRCW0402300RJNED	Vishay-Dale	RES, 300, 5%, 0.063 W, AEC-Q200 Grade 0, 0402	402
23	R13, R23	2	20	CRCW040220R0FKED	Vishay-Dale	RES, 20.0, 1%, 0.063 W, AEC-Q200 Grade 0, 0402	402
24	R25	1	0	RC0805JR-070RL	Yageo America	RES, 0, 5%, 0.125 W, 0805	805
25	T1	1	475uH	760390014	Würth Elektronik	Transformer, 475uH, SMT	10.05x4.19x6.73 mm
26	U1	1		SN6505BDBVR	Texas Instruments	Low-Noise 1 A, 420 kHz Transformer Driver, DBV0006A (SOT-23-6)	DBV0006A
27	U2, U3	2		ISO7741FDBQR	Texas Instruments		SSOP-16
28	U4, U5	2		LMG3526R030Q	Texas Instruments	650-V 30-mΩ GaN FET with Integrated Driver and Protection	VQFN52
29	U6	1		SN74AHC1G08DRLR	Texas Instruments	Single 2-Input Positive-AND Gate, DRL0005A, LARGE T&R	DRL0005A
30	U7	1		TPS71733DCKT	Texas Instruments	150mA, High PSRR, Low Quiescent Current, Low Noise LDO, DCK0005A (SOT-SC70-5)	DCK0005A
31	C32, C35	0	43pF	GCQ1555C1H430JB01D	MuRata	CAP, CERM, 43 pF, 50 V, +/- 5%, C0G/NP0, AEC-Q200 Grade 1, 0402	402
32	D1	0	650V	GB01SLT06-214	GeneSiC Semiconductor	Diode, Schottky, 650 V, 1 A, SMB	SMB
33	R7, R9	0	20.0k	CRCW040220K0FKED	Vishay-Dale	RES, 20.0 k, 1%, 0.063 W, 0402	402